



8NM65-FD

Preliminary

Power MOSFET

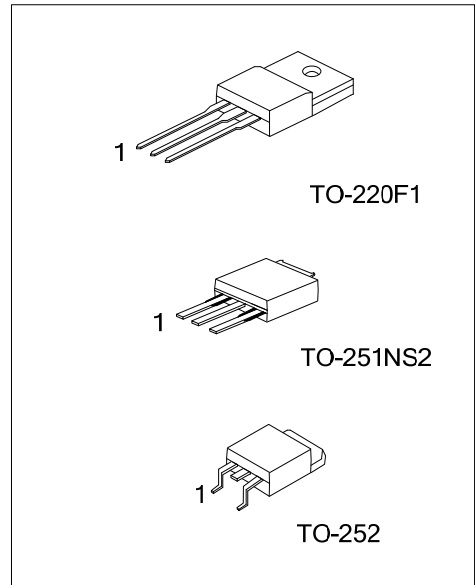
8A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

■ DESCRIPTION

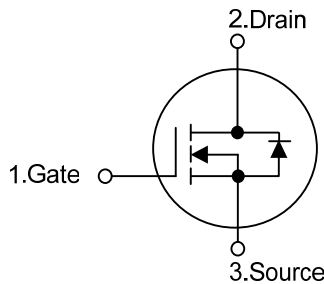
The **UTC 8NM65-FD** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} < 1.0 \Omega @ V_{GS} = 10V, I_D = 4.0A$
- * Fast Switching Capability
- * Avalanche Energy Tested
- * Improved dv/dt Capability, High Ruggedness



■ SYMBOL



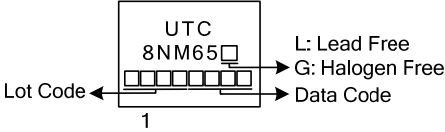
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8NM65L-TF1-T	8NM65G-TF1-T	TO-220F1	G	D	S	Tube
8NM65L-TMN2-T	8NM65G-TMN2-T	TO-251NS2	G	D	S	Tube
8NM65L-TN3-R	8NM65G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8NM65G-TF1-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TMN2: TO-251NS2 TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	145	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	14	V/ns
Power Dissipation	TO-220F1	P_D	48	W
	TO-251NS2/TO-252		62	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=66\text{mH}$, $I_{AS}=2.1\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 8.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251NS2/TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F1	θ_{JC}	2.6	$^\circ\text{C}/\text{W}$
	TO-251NS2/TO-252		2.0	$^\circ\text{C}/\text{W}$

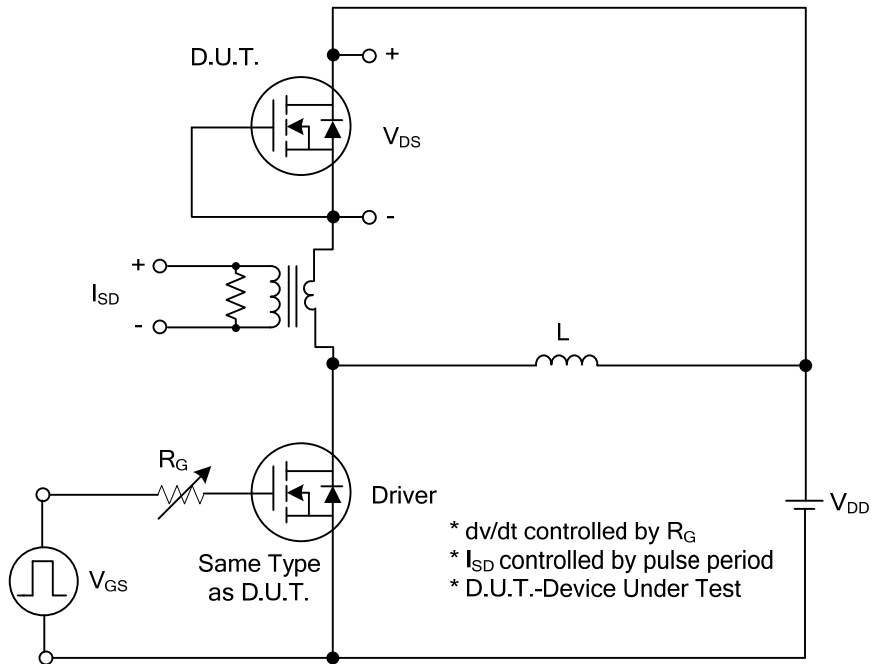
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 650V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 4.0A			1.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0 MHz		450		pF
Output Capacitance		C _{OSS}			346		pF
Reverse Transfer Capacitance		C _{RSS}			41		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =325V, V _{GS} =10V, I _D =3.25A, I _G =1mA (Note 1, 2)		25.4		nC
Gate to Source Charge		Q _{GS}			5		nC
Gate to Drain Charge		Q _{GD}			11		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =325V, V _{GS} =10V, I _D =3.25A, R _G =25Ω (Note 1, 2)		9		ns
Rise Time		t _R			23		ns
Turn-OFF Delay Time		t _{D(OFF)}			65		ns
Fall-Time		t _F			32		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				8	A
Maximum Body-Diode Pulsed Current		I _{SM}				32	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =8.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =8.0A, V _{GS} =0V, di/dt=100A/μs		115		ns
Body Diode Reverse Recovery Charge		Q _{rr}			0.52		μC

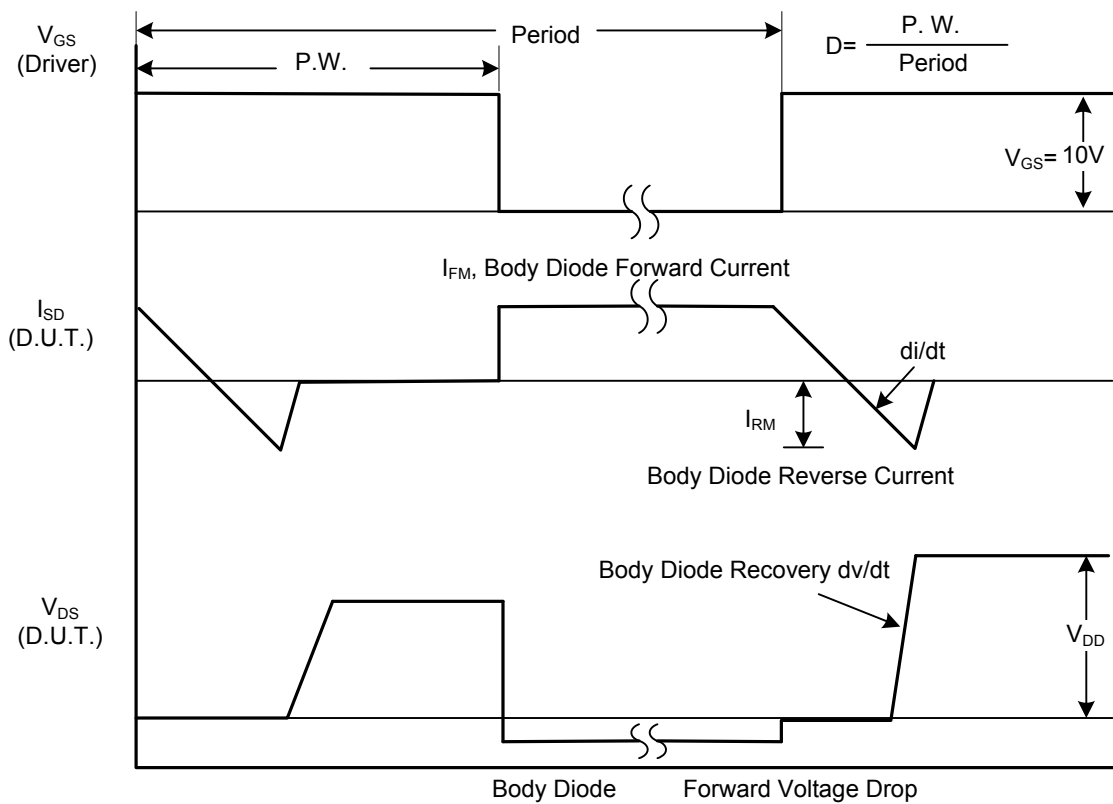
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

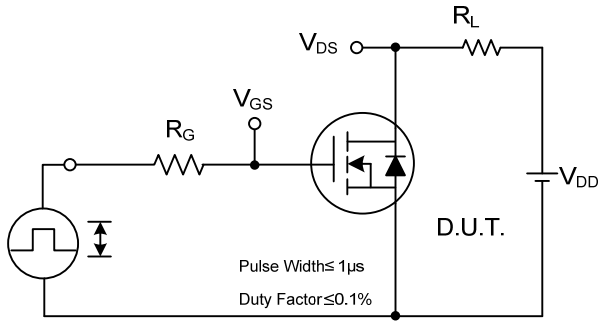


Peak Diode Recovery dv/dt Test Circuit

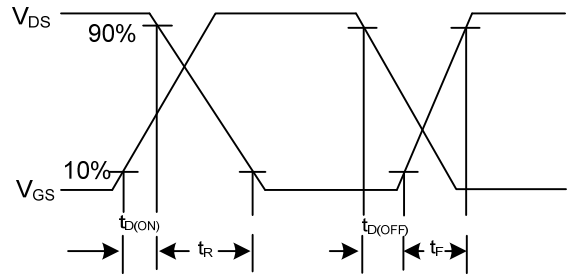


Peak Diode Recovery dv/dt Waveforms

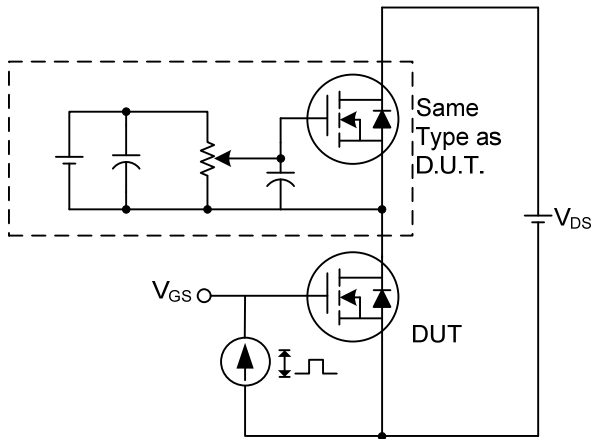
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



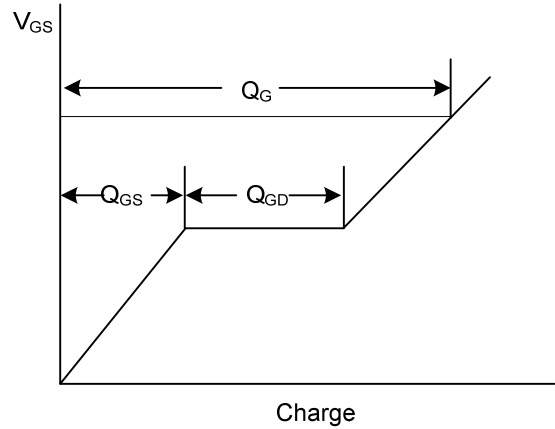
Switching Test Circuit



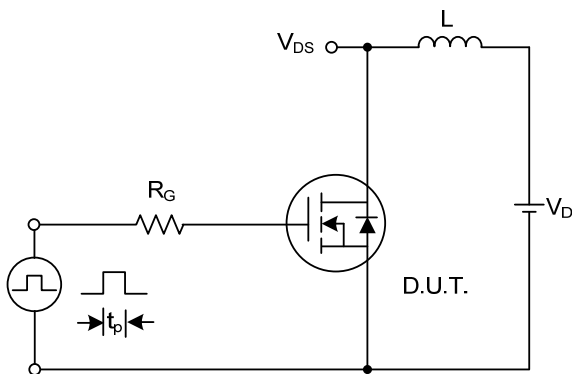
Switching Waveforms



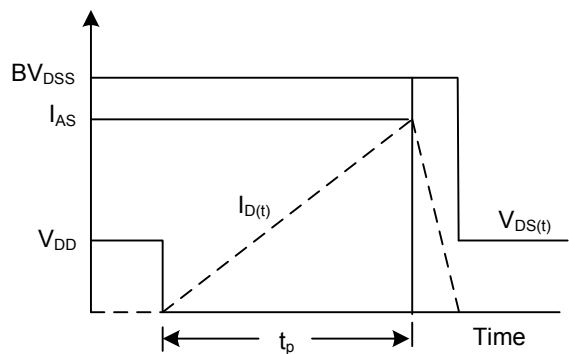
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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